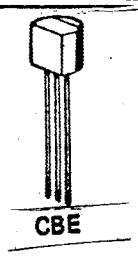
BC 485 BC 487 BC 489

NPN SILICON PLANAR EPITAXIAL TRANSISTORS

MICRO ELECTRONICS

BC485, BC487 and BC489 are NPN silicon planar epitaxial transistors designed for use as high voltage high current driver and output transistors.

CASE TO-92F



ABSOLUTE MAXIMUM RATINGS

		BC485	BC487	BC489
Collector-Base Voltage	V_{CBO}	45V	60V	80V
Collector-Emitter Voltage	V_{CEO}	45V	60V	80V
Emitter-Base Voltage	V_{EBO}		5V	
Collector Current	I_C		1A	
Total Power Dissipation @ T_A=25°C	P_{tot}		625mW	
@ T_C=25°C			1.5W	
Operating Junction & Storage Temperature	Tj, Tstg		-55 to +150°C	

ELECTRICAL CHARACTERISTICS AT T_A=25°C

PARAMETER		SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS	
Collector-Base Breakdown Voltage		BV_{CBO}	Note 1			V	I_C=0.1mA	I_E=0
Collector-Emitter Breakdown Voltage		BV_{CEO}				V	I_C=10mA	I_B=0
Emitter-Base Breakdown Voltage		BV_{EBO}				V	I_E=10μA	I_C=0
Collector Cutoff Current		I_{CBO}			100	nA	V_{CB}=V_{CBO}	I_E=0
Collector-Emitter Saturation Voltage		$V_{CE(SAT)}$*			0.5	V	I_C=500mA	I_B=50mA
Base-Emitter Saturation Voltage		$V_{BE(SAT)}$*			1.2	V	I_C=500mA	I_B=50mA
D.C. Current Gain	All groups	H_{FE}*	40				I_C=10mA	V_{CE}=2V
	All groups		60		400		I_C=100mA	V_{CE}=2V
	Group L		60		150		I_C=100mA	V_{CE}=2V
	Group A		100		250		I_C=100mA	V_{CE}=2V
	Group B		160		400		I_C=100mA	V_{CE}=2V
	All groups		15				I_C=1A	V_{CE}=5V
Current Gain-Bandwidth Product		f_T		75		MHz	I_C=50mA	V_{CE}=2V
Output Capacitance		Cob		12		pF	V_{CB}=10V	I_E=0
Input Capacitance		Cib		85		pF	V_{BE}=2V	I_C=0

Note 1 : equal to the values of the absolute maximum ratings.

* Pulse Test : Pulse Width=0.3ms, Duty Cycle=1%

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